

ABSTRACT OF THE DISCLOSURE

A semiconductor forming transistors on a semiconductor substrate includes a low concentration source/drain region
5 formed in the semiconductor substrate, a high concentration source/drain region formed in the source/drain region, a gate electrode formed on the substrate through gate oxide film, a P type body region formed under the gate electrode and placed between the source/drain regions and, plug contact portions
10 contacting the source/drain region and arranged in plural, and a source/drain electrode connecting to the source/drain region with contact through the contact portions.